
HZM4.3FA

Silicon Epitaxial Planar Zener Diode for Surge Absorb

HITACHI

ADE-208-468(Z)
Rev 0

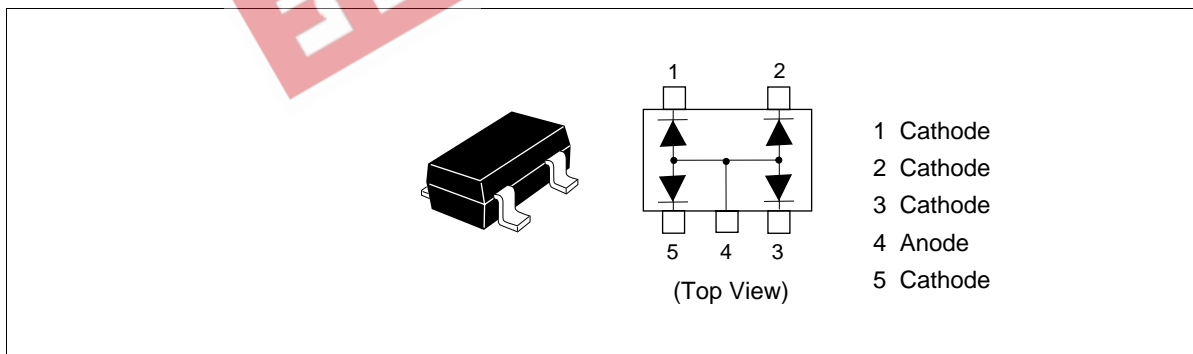
Features

- HZM4.3FA has four devices, and can absorb external + and -surge.
- MPAK-5 Package is suitable for high density surface mounting and high speed assembly.

Ordering Information

| Type No. | Laser Mark | Package Code |
|----------|------------|--------------|
| HZM4.3FA | 43A | MPAK-5 |

Outline



HZM4.3FA

Absolute Maximum Ratings (Ta = 25°C)

| Item | Symbol | Value | Unit |
|----------------------|------------------|-------------|------|
| Power dissipation | Pd ^{*1} | 200 | mW |
| Junction temperature | Tj | 150 | °C |
| Storage temperature | Tstg | -55 to +150 | °C |

Note: 1. Four device total, With P.C board.

Electrical Characteristics (Ta = 25°C) ^{*2}

| Item | Symbol | Min | Typ | Max | Unit | Test Condition |
|------------------------------|----------------|------|-----|------|------|-------------------------------------------------------------------|
| Zener voltage | V _z | 4.01 | — | 4.48 | V | I _z = 5 mA, 40ms pulse |
| Reverse current | I _R | — | — | 10 | μA | V _R = 1V |
| Capacitance | C | — | — | 150 | pF | V _R = 0V, f = 1 MHz |
| Dynamic resistance | r _d | — | — | 130 | Ω | I _z = 5 mA |
| ESD-Capability ^{*1} | — | 30 | — | — | kV | C = 150pF, R = 330 Ω, Both forward and reverse direction 10 pulse |

Notes: 1. Failure criterion ; I_R ≥ 10 μA at V_R = 1V.

2. Per one device.

Main Characteristic

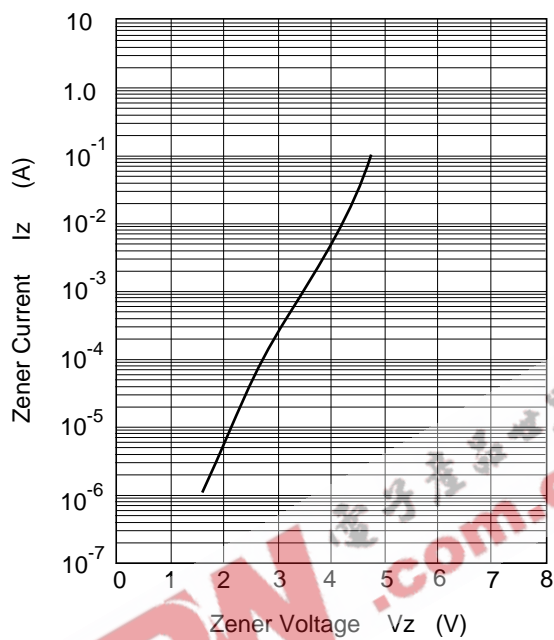


Fig.1 Zener current Vs. Zener voltage

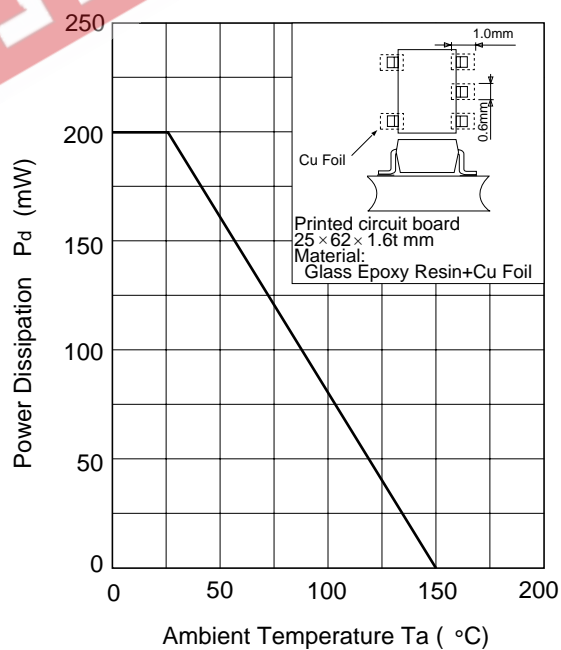


Fig.2 Power Dissipation Vs. Ambient Temperature

HZM4.3FA

Main Characteristic

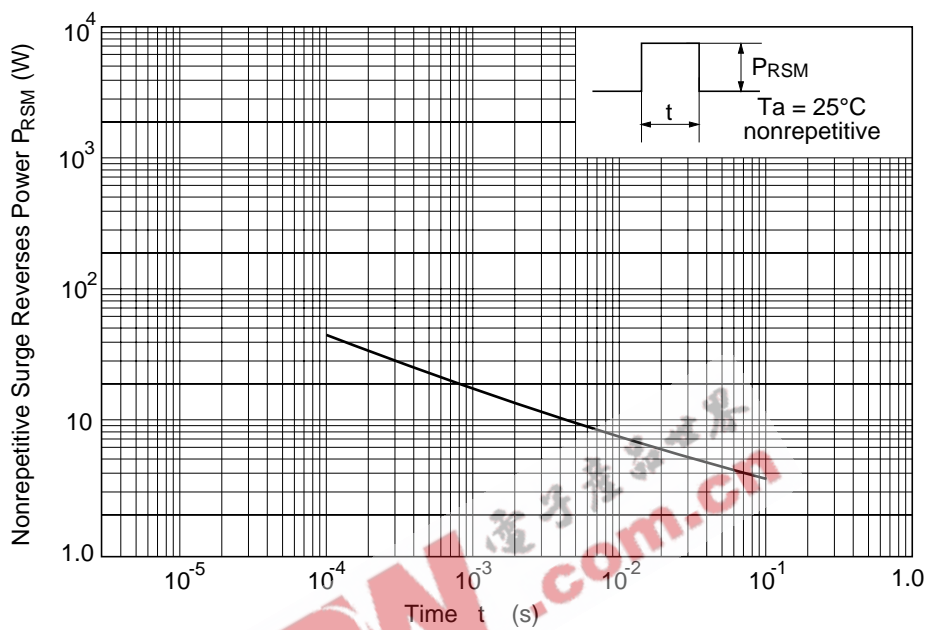


Fig.3 Surge Reverse Power Ratings

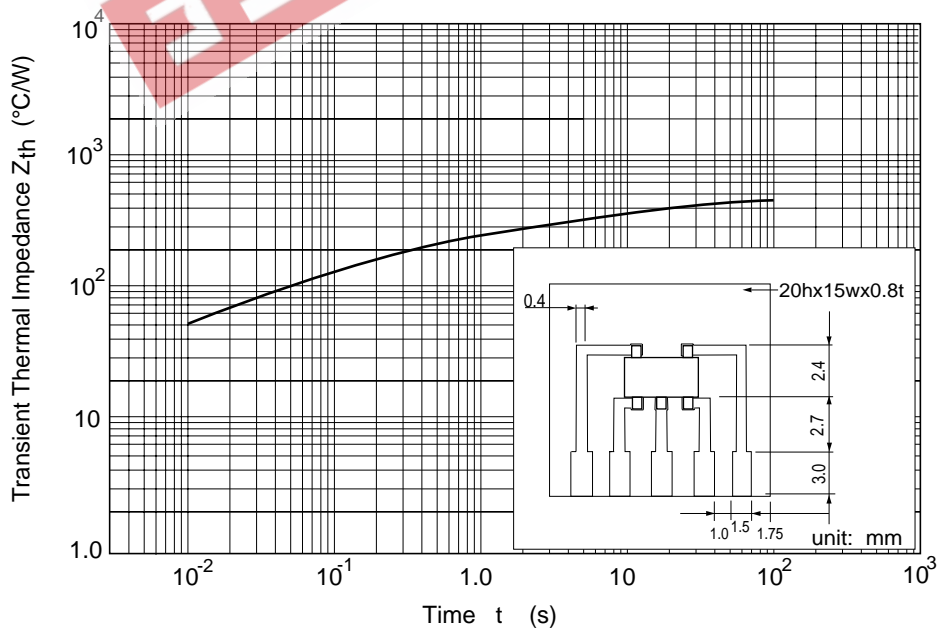
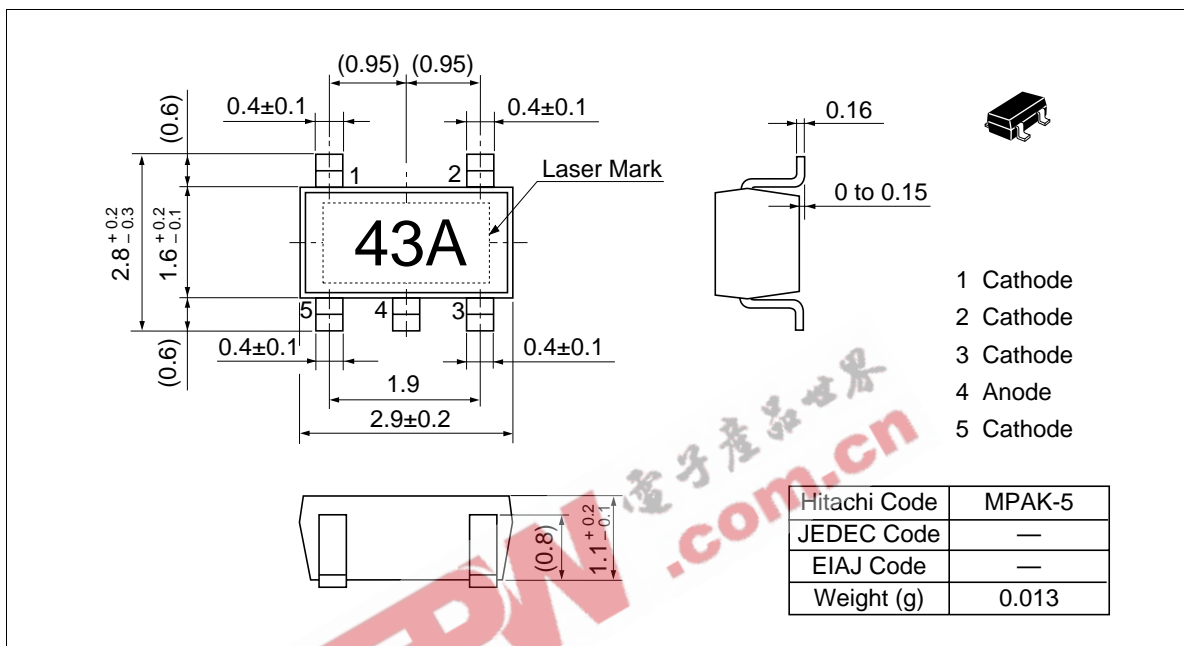


Fig.4 Transient Thermal Impedance

Package Dimensions

Unit : mm



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